

# FUJITSU

## MICROELECTRONICS

### CMOS 32,768-BIT UV ERASABLE AND ELECTRICALLY PROGRAMMABLE READ ONLY MEMORY

# MBM27C32-25

# MBM27C32-30

## ADVANCE INFORMATION

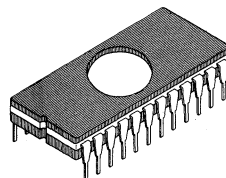
#### DESCRIPTION

The Fujitsu MBM27C32 is a high speed 32,768-bit static Complementary MOS erasable and electrically reprogrammable read only memory (EPROM). It is especially suited for applications where the extremely low power consumption of CMOS is essential.

A 24-pin dual in-line package with a transparent lid is used to package the MBM27C32. The transparent lid allows the user to expose the device to ultraviolet light

in order to erase the memory bit pattern previously programmed. At the completion of erasure, a new pattern can be programmed into the memory.

The MBM27C32 is fabricated using CMOS double polysilicon gate technology with single transistor stacked gate cells. It is organized as 4096 words by 8-bits for use in microprocessor applications. Single +5V operation greatly facilitates its use in systems.

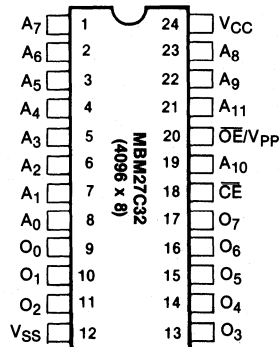


**CERDIP PACKAGE**  
**DIP-24C-C02**

#### FEATURES

- CMOS Power Consumption:  
500 $\mu$ W max. (Standby)  
40mW/MHz (Active)
- Organized as 4096 words by 8-bits, fully decoded
- Utilizes the same simple programming requirements as MBM2732A
- Single location programming
- Programming pulse may be reduced to 25 ns to cut programming time in half
- No clock required, fully static operation
- TTL compatible inputs/outputs
- Three-state output with OR-tie capability
- Output Enable ( $\overline{OE}$ ) pin simplifies memory expansion
- Fast Access Time:  
MBM27C32-25 250 ns max.  
MBM27C32-30 300 ns max.
- Single +5V operation
- Jedec standard 24-pin DIP package
- Pin and function compatible with 2732A-type devices

#### PIN ASSIGNMENT



***THIS IS PRELIMINARY INFORMATION  
FOR A NEW PRODUCT TO BE  
INTRODUCED DURING 1982. THIS IS  
NOT A FINAL SPECIFICATION.  
PARAMETRIC LIMITS ARE SUBJECT  
TO CHANGE.***

This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields. However, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.